

RECEIVED
CENTRAL FAX CENTER

DEC 01 2005



Ryan, Mason & Lewis, LLP
ATTORNEYS AT LAW
1300 POST ROAD
SUITE 205
FAIRFIELD, CT 06824

Receipt in the USPTO is hereby acknowledged of:

Information Disclosure Statement
Form PTO-1449 and Cited Reference(s)

RECEIVED
JAN 30 2004

January 21, 2004
YOR920030175US1
1500-419 (MIC)



FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Applicant(s): Allen et al.
Docket No.: YOR920030175US1
Serial No.: 10/661,041
Filing Date: September 12, 2003
Group: 2811

RECEIVED
CENTRAL FAX CENTER

DEC 01 2005

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO

OTHER DOCUMENTS

EXAMINER INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
		Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 μ m Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
		Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
		DellaGuardia et al., "193 Lithography and RELACST TM Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
		Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
		Satou et al., "Sub-0.10 μ m Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Page 1 of 1

FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Applicant(s): Allen et al.
Docket No.: YOR920030175US1
Serial No.: 10/661,041
Filing Date: September 12, 2003
Group: 2811



U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO

OTHER DOCUMENTS

EXAMINER INITIAL	REF. NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<u>ca</u>		Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 μ m Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
<u>ca</u>		Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
<u>ca</u>		DellaGuardia et al., "193 Lithography and RELACS TM Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
<u>ca</u>		Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
<u>ca</u>		Satou et al., "Sub-0.10 μ m Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Page 1 of 1



Ryan, Mason & Lewis, LLP
ATTORNEYS AT LAW
1300 POST ROAD
SUITE 205
FAIRFIELD, CT 06824

Receipt in the USPTO is hereby acknowledged of:

RECEIVED
MAR 08 2005

Information Disclosure Statement
Form PTO-1449 and Cited Reference(s)



February 23, 2005
YOR920030175US1
1500-419 (MJC)

FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Applicant(s): Allen et al.
 Docket No.: YOR920030175US1
 Serial No.: 10/661,041
 Filing Date: September 12, 2003
 Group: 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE
					IF APPROPRIATE
_____	5,753,418	05/19/98	Tsai et al.	430/313	
_____	6,009,888	01/04/00	Ye et al.	134/1.3	
_____	6,316,167	11/13/01	Angelopoulos et al.	430/313	
_____	6,387,798	05/14/02	Loke et al.	438/623	
_____	6,514,867	02/04/03	Hui et al.	438/713	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION	
					YES	NO
_____	EP 0 236 220 A1	13/04/88	Europe			

OTHER DOCUMENTS

EXAMINER INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.			
_____		Celii et al., "Process Characterization for Tapered Contact Etch," J. Vac. Sci. Technol. B 19(5), American Vacuum Society, Pgs. 1845-1851 (Sept/Oct 2001).			
_____		Mahorowala et al., "Tunable Anti-Reflective Coatings with Built-In Hard Mask Properties Facilitating Thin Resist Processing," Proceedings of the SPIE, Vol. 4343, Pgs. 306-316 (2001).			

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Page 1 of 1

FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Applicant(s): Allen et al.
Docket No.: YOR920030175US1
Serial No.: 10/661,041
Filing Date: September 12, 2003
Group: 2811

U.S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
INITIAL					
<u>an</u>	5,753,418	05/19/98	Tsai et al.	430/313	
<u>an</u>	6,009,888	01/04/00	Ye et al.	134/1.3	
<u>an</u>	6,316,167	11/13/01	Angelopoulos et al.	430/313	
<u>an</u>	6,387,798	05/14/02	Loke et al.	438/623	
<u>an</u>	6,514,867	02/04/03	Hui et al.	438/713	

FOREIGN PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO
INITIAL					
	EP 0 236 220 A1	13/04/88	Europe		

OTHER DOCUMENTS

EXAMINER	REF. NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
INITIAL		
		Celli et al., "Process Characterization for Tapered Contact Etch," J. Vac. Sci. Technol. B 19(5), American Vacuum Society, Pgs. 1845-1851 (Sept/Oct 2001).
		Mahorowala et al., "Tunable Anti-Reflective Coatings with Built-In Hard Mask Properties Facilitating Thin Resist Processing," Proceedings of the SPIE, Vol. 4343, Pgs. 306-316 (2001).

Examiner

6-16-05
Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Page 1 of 1